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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09 900,962	07 10 2001	Hisayuki Miki	Q61744	7972

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EXAMINER

MULPURI, SAVITRI

ART UNIT	PAPER NUMBER
2812	

DATE MAILED: 11/15/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No. 09/900,962	Applicant(s) Miki et al
	Examiner Savitri Mulpuri	Art Unit 2812
		
<i>-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --</i>		
Period for Reply		
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE <u>3</u> MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.		
<p style="margin-left: 20px;">- Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.</p> <p style="margin-left: 20px;">- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.</p> <p style="margin-left: 20px;">If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.</p> <p style="margin-left: 20px;">- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).</p> <p style="margin-left: 20px;">- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).</p>		
Status		
1) <input checked="" type="checkbox"/> Responsive to communication(s) filed on <u>Oct 3, 2002</u>		
2a) <input type="checkbox"/> This action is FINAL . 2b) <input checked="" type="checkbox"/> This action is non-final.		
3) <input type="checkbox"/> Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.		
Disposition of Claims		
4) <input checked="" type="checkbox"/> Claim(s) <u>1-14</u> is/are pending in the application.		
4a) Of the above, claim(s) <u>14</u> is/are withdrawn from consideration.		
5) <input type="checkbox"/> Claim(s) _____ is/are allowed.		
6) <input checked="" type="checkbox"/> Claim(s) <u>1-13</u> is/are rejected.		
7) <input type="checkbox"/> Claim(s) _____ is/are objected to.		
8) <input type="checkbox"/> Claims _____ are subject to restriction and/or election requirement.		
Application Papers		
9) <input type="checkbox"/> The specification is objected to by the Examiner.		
10) <input type="checkbox"/> The drawing(s) filed on _____ is/are a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).		
11) <input type="checkbox"/> The proposed drawing correction filed on _____ is: a) approved b) disapproved by the Examiner. If approved, corrected drawings are required in reply to this Office action.		
12) <input type="checkbox"/> The oath or declaration is objected to by the Examiner.		
Priority under 35 U.S.C. §§ 119 and 120		
13) <input type="checkbox"/> Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).		
a) All b) Some* c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. _____. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).		
*See the attached detailed Office action for a list of the certified copies not received.		
14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).		
a) The translation of the foreign language provisional application has been received.		
15) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.		
Attachment(s)		
1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)		
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)		
3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s). <u>3</u>		
4) Interview Summary (PTO-413) Paper No(s). _____		
5) Notice of Informal Patent Application (PTO-152)		
6) Other _____		

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DETAILED ACTION

This action is in response to the applicant's election of method claims 1-13, filed on 10/3/02.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

Claims 1-13 are rejected under 35 U.S.C. 102(a) as being anticipated by Onomura et al..

Onomura et al discloses a method of making a P-type gallium nitride based semiconductor by the following process steps: providing a substrate, growing device layer including p-type GaN as top layer; depositing metal layers such as Pt, Au, Ni etc. and subsequently annealing the structure having p-type GaN and metal. Onomura et al further teaches forming metal layer with thickness of about 10 nm to 50 nm and annealing at the temperature of 350 C (see col. 3, lines 3-55). Though, Onomura et al do not teach stripping the metal layer, it is inherent in the invention of Onomura the metal layer Pt or Ni has to be stripped to make the metal pattern.

Claims 1-13 are rejected under 35 U.S.C. 102(a) as being anticipated by Ota et al.

Ota et al discloses a method of making semiconductor device by the following process steps: Forming p-GaN layer on a substrate; depositing Ni layer "115" on p-GaN substrate; annealing at 300-800 C and removing the Ni layer. Ota clearly mention that Ni acts as a catalyst

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for trapping hydrogen Mg doped p-GaN layer, and also not to dissociate nitrogen from the p-GaN layer(see abstract and fig. 6 and 7 and col. 15, lines 60-67 and col. 12, lines 1-15).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Mulpuri whose telephone number is 703- 305-5184. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703308-0956..



SAVITRI MULPURI
PRIMARY EXAMINER